HD31952
SOLID STATE POWER AMPLIFIER

FEATURES

Small form factor benchtop system
Class AB linear GaAsFET design
Instantaneous wide bandwidth
Suitable for all single channel modulation standards
Built-in protection circuits
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	26.5 - 40 GHz	
Power Output @ Psat	34 dBm Min	CW
Output Power @ P1dB G.C.P.	30 dBm Min	
Linear Gain	36 dB Min	
Power Gain Flatness	±2.2 dB Typ / ±3.5 dB Max	Constant input power
Input Return Loss	-10 dB Typ	Relative to 50 Ohm
Noise Figure	6 dB Typ	
Harmonics	-20 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC	
Power Consumption	50 Watt Max	At rated Pout
Max Input Power Protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	∞ : 1	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +70 °C	
Relative Humidity	5 to 95 %	Non-condensation

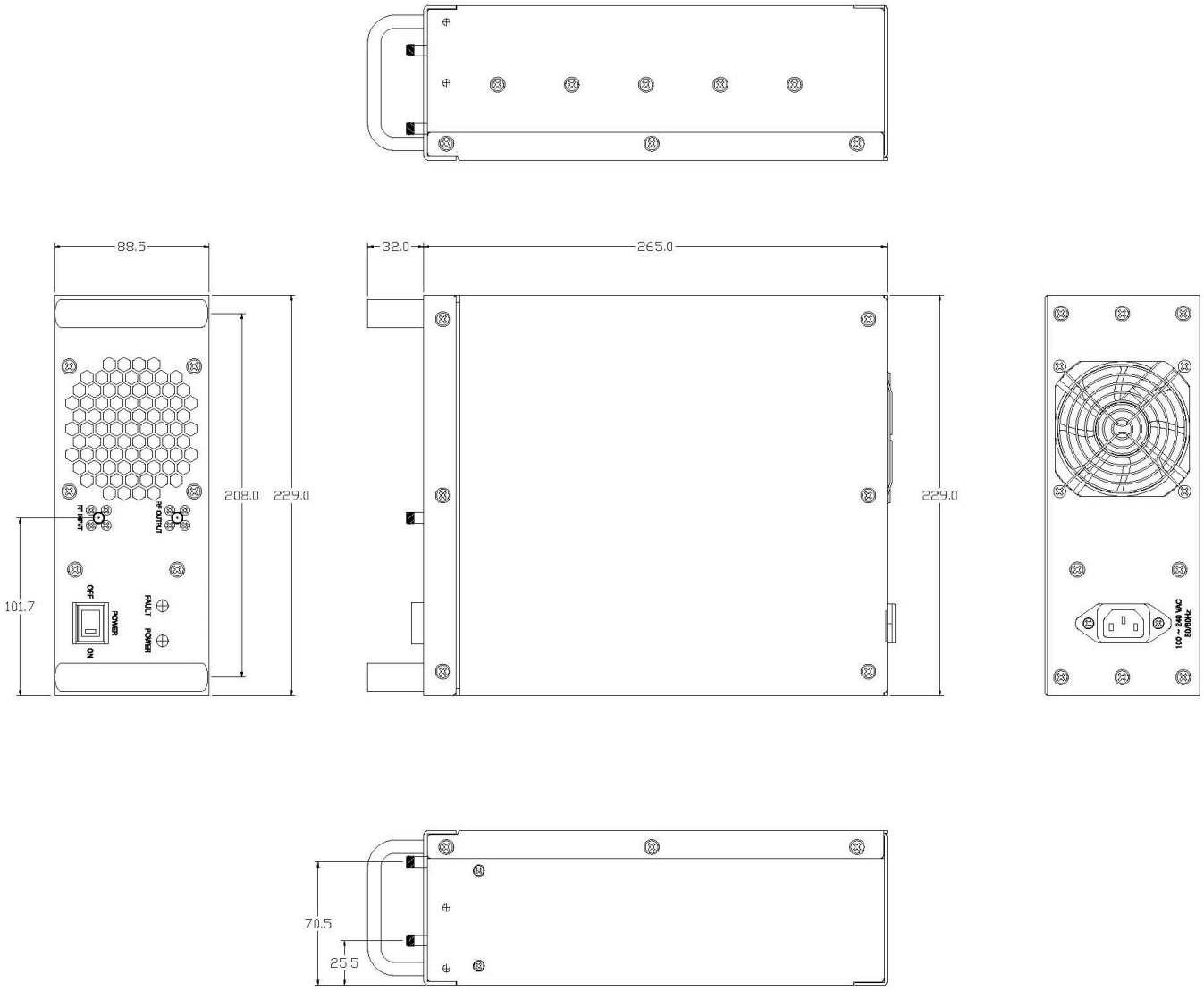
MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	265 x 88 x 229 mm	Excluding handles
Weight	6 kg.	
RF Connectors In/Out	2.9 mm (K / air type) Female	Front Panel Standard
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	
Cooling	Built in Fan Cooling	
OPTIONAL: Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485 Optional GPIB Interface	Option available in a 2U chassis

332C Dante Ct. Holbrook, NY 11741 Phone: 631-588-3877 Fax: 631-648-0518
www.rfamplifiers.com www.rfcomp.com sales@hdcom.com

HD31952
SOLID STATE POWER AMPLIFIER

BENCH TOP CHASSIS



332C Dante Ct. Holbrook, NY 11741 Phone: 631-588-3877 Fax: 631-648-0518
www.rfamplifiers.com www.rfcomp.com sales@hdcom.com